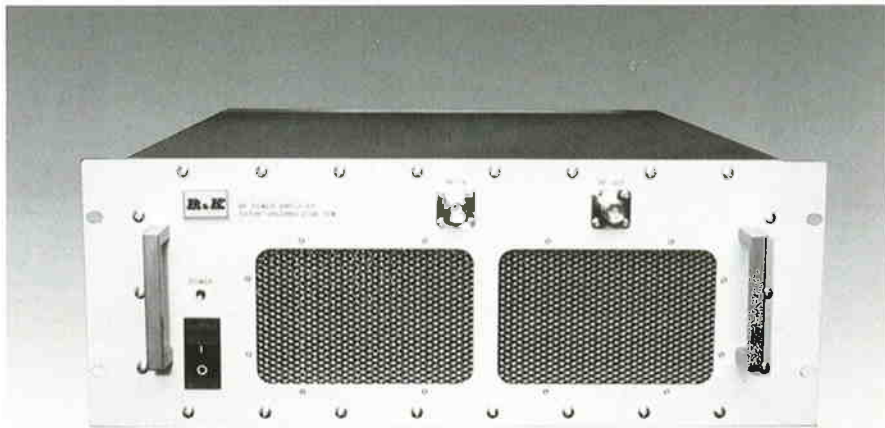




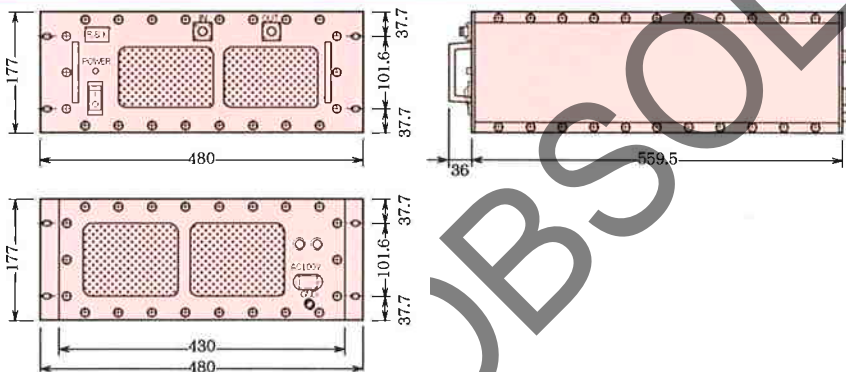
MICROWAVE GaAs FET AMPLIFIER

MODEL R&K A1026-2740R

- BROADBAND FREQUENCY : 1000 ~ 2600MHz
- HIGH POWER : 10W min. (@1dB Comp.)
- HIGH RELIABILITY GaAs FET CONSTRUCTION
- FOR COMMUNICATIONS TEST EQUIPMENT
- WORLD BROADEST BAND MODEL



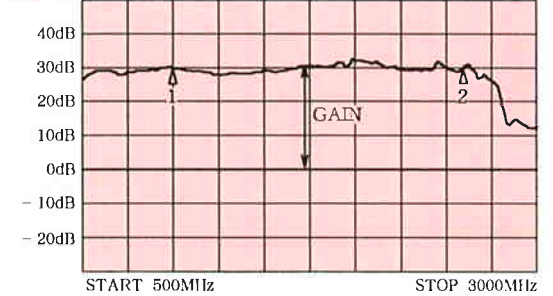
DIMENSION



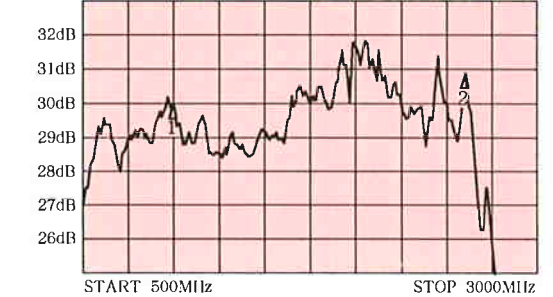
SPECIFICATIONS

1. Input/Output Frequency Range 1000~2600MHz (min.)
2. Small Signal Gain +27dB (min.)
3. Power Gain @1dB Compression +26dB (min.)
4. Power Gain Flatness ± 2.0 dB (max.)
5. Power Output (@1dB Comp.) 10W (min.)
6. Amplifier Operation Mode Class A Linear
7. 2 Tone 3rd Order Intercept Point +50dBm (typ.)
8. Input/Output Impedance 50 Ω Nominal
9. Input VSWR 2.0 (max.)
10. Output VSWR 3.0 (max.)
11. Harmonics -18dBc (max.) @ Full Power
12. Spurious -60dBc (max.) @ Full Power
13. Input Noise Figure 12dB (typ.)
14. Output Power Duty Ratio 100% C.W.
15. Connectors RF Input N - Female
RF Output N - Female
16. AC Power Supply Input 100V, AC \cdot 50/60Hz, 4A (max.)
17. Cooling Integral Forced Air Cooling
18. Operating Temperature -10 $^{\circ}$ C ~ +45 $^{\circ}$ C
19. Storage Temperature -15 $^{\circ}$ C ~ +65 $^{\circ}$ C
20. Protection Circuits Output Overdrive
Thermal Overload

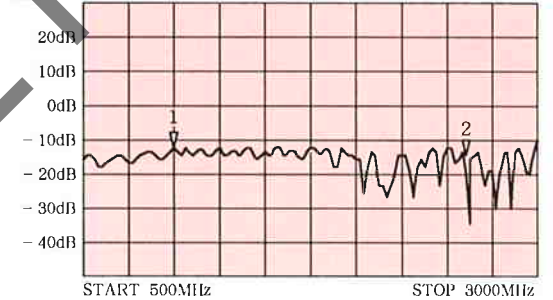
SMALL SIGNAL GAIN



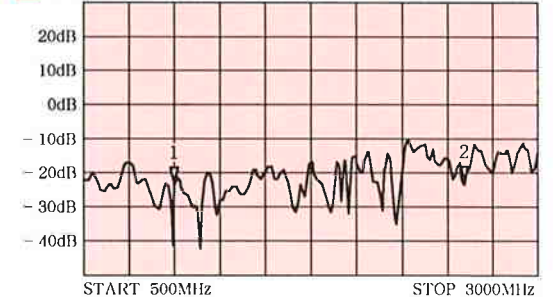
GAIN FLATNESS



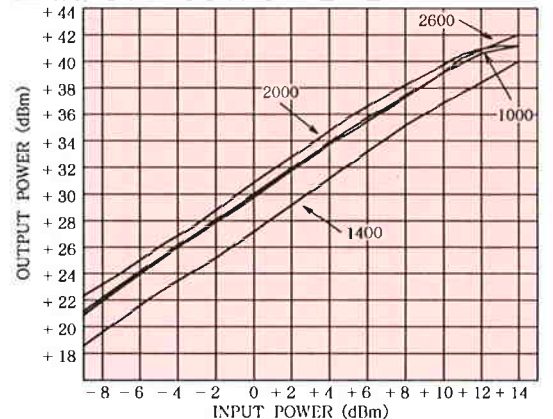
INPUT RETURN LOSS



OUTPUT RETURN LOSS



INPUT - OUTPUT LINEARITY



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Phone:0545-64-0559 FAX:0545-64-0507